

East Search
(paper no. 10)

L Number	Hits	Search Text	DB	Time stamp
-	867	(438/95).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/21 13:42
-	1	((438/95).CCLS.) and pcram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 10:59
-	6	("5751012" "5761115" "5789277" "5896312" "5914893" "6084796").PN.	USPAT	2002/08/20 10:57
-	0	6348365.URPN.	USPAT	2002/08/20 10:57
-	1	chalcogenide and pcram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:00
-	3	pcram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:02
-	1	((438/95).CCLS.) and fast adj ion adj conductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:03
-	30	((438/95).CCLS.) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:33
-	9	("4922319" "5022742" "5070383" "5268316" "5272097" "5355301" "5407851" "5441907" "5567644").PN.	USPAT	2002/08/20 11:11
-	3	5854102.URPN.	USPAT	2002/08/20 11:11
-	761	chalcogenide and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:34
-	84	fast adj ion adj conductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:34
-	235	(chalcogenide and memory) and memory adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:35
-	25	(chalcogenide and memory) and memory adj cell with stack\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:36
-	1	micron.as. and pcram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:36
-	22	(fast adj ion adj conductor) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:53

8	(PMC programmable adj metallization) and fast adj ion and chalcogenide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 12:00
2	first near ("5751012" "5761115" "5789277" "5896312" "5914893" "6084796").PN.) memory adj cell with chalcogenide and second near3 memory adj cell with chalcogenide	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 12:08
0	first near3 memory adj cell with chalcogenide and second near3 memory adj cell with chalcogenide	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 12:10
1	first near3 memory with conductor and second near3 memory with conductor and chalcogenide with conductor	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 12:11
13	memory adj cell with conductor with chalcogenide	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:11
394	chalcogenide with ion	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:24
8	(chalcogenide with ion) and memory adj cell	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:12
2	("3363239" "3482217").PN.	USPAT	2002/08/20 13:13
1	6084796.URPN.	USPAT	2002/08/20 13:14
19	("3271591" "3530441" "3715634" "3765956" "3846767" "3875566" "3886577" "3980505" "3988720" "4199692" "5177567" "5296835" "5500532" "5596500" "5646629" "5761115" "5912839" "5914893" "5933365").PN.	USPAT	2002/08/20 13:14
0	6418049.URPN.	USPAT	2002/08/20 13:14
1920	chalcogenide with metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:24
54	(chalcogenide with metal) and memory adj cell	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:26
2	5825046.pn.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:39
0	two adj chalcogenide adj layer	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:40

	3	second adj chalcogenide adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/08/20 13:52
	18	("4590589" "5208177" "5250459" "5264725" "5296716" "5451811" "5485031" "5486707" "5521423" "5631862" "5760462" "5761115" "5789277" "5789758" "5792594" "5920788" "6025220" "6077729").PN.		2002/08/20 13:50
	0	6284643.URPN.	USPAT	2002/08/20 13:50
	0	2002us-0102788.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:56
	37	("6015977" "6077729" "6284643" "5825046" "5912839" "5933365" "6418049" "6348365" "6426891" "5831276" "5789758" "6189582" "5998244" "5970336" "5854102" "5837564" "5335219" "5296716" "5814527" "5789277") [pn]	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 13:56
	1	us-20020102788-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 14:00
	1	us-20020106849-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 14:02
	12	("6015977" "6077729" "6284643" "5970336" "6426891" "6418049" "5912839") [pn]	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 14:56
	157	function with access adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 15:10
	0	conventionally adj used with (couple coupled connected connect) with access adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 15:00
	2	conventionally adj used with access adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 15:07
	10	typically adj used with access adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 15:09
	0	generally adj used with access adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 15:09
	96	(function with access adj transistor) and access adj transistor with memory adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 15:10

-	50	function near3 access adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 15:54
-	1	1999jp-0305518.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 15:54
-	1	2002-190074.NRAN.	DERWENT	2002/08/20 15:55
-	23	(US-6426891-\$ or US-6418049-\$ or US-6348365-\$ or US-6284643-\$ or US-6189582-\$ or US-6077729-\$ or US-6015977-\$ or US-5998244-\$ or US-5970336-\$ or US-5933365-\$ or US-5912839-\$ or US-5854102-\$ or US-5837564-\$ or US-5831276-\$ or US-5825046-\$ or US-5814527-\$ or US-5789758-\$ or US-5789277-\$ or US-5335219-\$ or US-5296716-\$).did. or (US-20020102788-\$ or US-20020106849-\$).did. or (US-6348365-\$).did.	USPAT; US-PGPUB; DERWENT	2002/08/20 16:06
-	19	((US-6426891-\$ or US-6418049-\$ or US-6348365-\$ or US-6284643-\$ or US-6189582-\$ or US-6077729-\$ or US-6015977-\$ or US-5998244-\$ or US-5970336-\$ or US-5933365-\$ or US-5912839-\$ or US-5854102-\$ or US-5837564-\$ or US-5831276-\$ or US-5825046-\$ or US-5814527-\$ or US-5789758-\$ or US-5789277-\$ or US-5335219-\$ or US-5296716-\$).did. or (US-20020102788-\$ or US-20020106849-\$).did. or (US-6348365-\$).did.) and access	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 16:07
-	1	((US-6426891-\$ or US-6418049-\$ or US-6348365-\$ or US-6284643-\$ or US-6189582-\$ or US-6077729-\$ or US-6015977-\$ or US-5998244-\$ or US-5970336-\$ or US-5933365-\$ or US-5912839-\$ or US-5854102-\$ or US-5837564-\$ or US-5831276-\$ or US-5825046-\$ or US-5814527-\$ or US-5789758-\$ or US-5789277-\$ or US-5335219-\$ or US-5296716-\$).did. or (US-20020102788-\$ or US-20020106849-\$).did. or (US-6348365-\$).did.) and access adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 16:13
-	1	((US-6426891-\$ or US-6418049-\$ or US-6348365-\$ or US-6284643-\$ or US-6189582-\$ or US-6077729-\$ or US-6015977-\$ or US-5998244-\$ or US-5970336-\$ or US-5933365-\$ or US-5912839-\$ or US-5854102-\$ or US-5837564-\$ or US-5831276-\$ or US-5825046-\$ or US-5814527-\$ or US-5789758-\$ or US-5789277-\$ or US-5335219-\$ or US-5296716-\$).did. or (US-20020102788-\$ or US-20020106849-\$).did. or (US-6348365-\$).did.) and decoder	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 16:23

-	3	((US-6426891-\$ or US-6418049-\$ or US-6348365-\$ or US-6284643-\$ or US-6189582-\$ or US-6077729-\$ or US-6015977-\$ or US-5998244-\$ or US-5970336-\$ or US-5933365-\$ or US-5912839-\$ or US-5854102-\$ or US-5837564-\$ or US-5831276-\$ or US-5825046-\$ or US-5814527-\$ or US-5789758-\$ or US-5789277-\$ or US-5335219-\$ or US-5296716-\$).did. or (US-20020102788-\$ or US-20020106849-\$).did. or (US-6348365-\$).did.) and (ag silver) with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 16:27
-	31	peripheral adj circuit with memory with access adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 16:30
-	1	6426891.pn. and smoothing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/21 13:42